



3DD101

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications					Test Condition
			A	B	C	D	E	
Collector-Emitter Voltage	V _{CEO}	V	100	150	200	250	300	
Emitter-Base Voltage	V _{EBO}	V	4					
Max. Collector Current	I _{CM}	A	5					
Max. Collector Dissipation	P _{CM}	W	50					Tc:75°C
Junction Temperature	T _{jm}	°C	175					
Storage Temperature	T _{stg}	°C	-55~+175					
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:1.0					V _{CE} =50V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:0.8			Max.:1.5		I _C =2.5A,I _B =0.25A
DC Current Gain	h _{FE}		Min.:20,Max.:120					V _{CE} =5V,I _C =2A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	I _C =1mA
			100	150	200	250	300	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	4					I _E =1mA

hFE Colored:

Color	Brown	Red	Orange
h _{FE}	20~40	40~80	80~120

Outline and Dimensions: